

ABSTRACT

[0042] A semiconductor device (1) has a fin (2) and a multiple gate electrode (3) over the fin (2), the multiple gate electrode (3) being a layer of gate electrode material with a substantially planar surface (13b) to support a patterned mask (14a), the mask (14a) having a uniform thickness and a planar surface controlling the patterning dimensions of the patterned mask (14a) .